

What is claimed is:

1. A semiconductor device for comparing an input address with a stored repair address, comprising:

5 a signal controller for generating control signals;
 an address latch unit in response to the control signals for latching the input address;

 N number of M-bit address comparators, each for comparing the input address with the stored repair address;

10 a comparator delay modeling block for delaying the control signal for a predetermined time; and

 a repair circuit controller in response to the delayed control signal output from the comparator delay modeling block for generating one of a repair address enable signal and a
15 normal address enable signal based on a comparison result of an address comparator.

2. The semiconductor device as recited in claim 1, further comprising a comparator initialization unit for
20 generating an enable signal to enable and initialize an N number of M-bit address comparators.

3. The semiconductor device as recited in claim 2, wherein each of the M-bit address comparators includes:

25 a fuse enabling means for outputting a fuse enabling signal and receiving the fuse enabling signal in response to whether an enabling fuse included in the fuse enabling means

is blown out or not;

a plurality of unit repair address comparing means for respectively comparing each bit of the input address which is latched in the address latching means with each bit of the
5 stored repair address which is stored in the repair address comparing means; and

a signal combination means for outputting the repair signal in response to results of the plurality of unit repair address comparing means,

10 wherein the signal combination means is enabled by the fuse enabling signal.

4. The semiconductor device as recited in claim 3, the fuse enabling means includes:

15 a first MOS transistor connected to a supply voltage, gates of the first MOS transistor being supplied with a fuse reset signal;

a second MOS transistor connected to a ground voltage, gates of the second MOS transistor being supplied with the
20 fuse reset signal;

an enabling fuse coupled between the first and second MOS transistors;

a first inverter for receiving a signal supplied between the enable fuse and the second MOS transistor;

25 a third MOS transistor connected between an input terminal of the first inverter and the ground voltage, gate of the third MOS transistor being coupled to an output terminal

of the first inverter;

a second inverter for receiving an output signal from the first inverter;

a first transmission gate for outputting the enabling
5 signal as the fuse enabling signal by turning on when the enable fuse is blown out; and

a second transmission gate for outputting the supplied
signal between the enable fuse and the second MOS transistor
as the fuse enabling signal by turning on when the enable fuse
10 is not blown out,

wherein the first and the second transmission gates are controlled by output signals from the first and the second inverters.

15 5. The semiconductor device as recited in claim 4, the fuse enabling means further includes a delay means for delaying the enabling signal for a predetermined time.

20 6. The semiconductor device as recited in claim 5, the unit repair address comparing means includes:

a fourth MOS transistor connected to a supply voltage, gates of the fourth MOS transistor being supplied with a fuse reset signal;

a fifth MOS transistor connected to a ground voltage,
25 gates of the fifth MOS transistor being supplied with the fuse reset signal;

an address fuse coupled between the fourth and fifth MOS

transistors;

a third inverter for receiving a signal supplied between the address fuse and the fifth MOS transistor;

a sixth MOS transistor connected between an input
5 terminal of the third inverter and the ground voltage, gate of the sixth MOS transistor being coupled to an output terminal of the third inverter;

a fourth inverter for receiving an output signal from the first inverter;

10 a third transition gate for outputting one bit of the input address to the signal combination means as a comparison signal by turning on if the address fuse is blown out; and

a fourth transition gate for outputting one bit of the inverse input address to the signal combination means as a
15 comparison signal by turning on if the address fuse is not blown out.

7. The semiconductor device as recited in claim 6, the signal combination means includes:

20 a plurality of first NOR gates for receiving the fuse enabling signal and the comparison signal output from the plurality of unit repair address comparing means;

a plurality of first NAND gates for receiving output signals from the plurality of first NOR gates;

25 a second NOR gate for receiving output signals from the plurality of first NAND gates; and

a fifth inverter for receiving an output signal from the

second NOR gate and outputting the repair signal.

8. The semiconductor device as recited in claim 7,
further comprising a repair address comparison replica which
5 includes:

a third NOR gate for delaying the enabling signal by a
delay time of the comparison signal output from the plurality
of unit repair address comparing means by a delaying value of
the plurality of first NOR gate;

10 a second NAND gate for delaying an output signal from
the third NOR gate by a delay time of the plurality of first
NOR gate; and

a fourth NOR gate for delaying an output signal from the
second NAND gate by a delay time of the second NOR gate.

15

9. The semiconductor device as recited in claim 8, the
repair address comparison replica further includes an output
controller for adjusting phase and level of an output signal
from the fourth NOR gate in order to equalize phase and level
20 of an output signal from the fourth NOR gate with phase and
level of the repair signal which is delivered from the repair
address comparing means to the repair circuit controller.

10. The semiconductor device as recited in claim 3, the
25 fuse enabling means includes:

a first MOS transistor connected to a supply voltage,
gates of the first MOS transistor being supplied with a fuse

reset signal;

a second MOS transistor connected to a ground voltage, gates of the second MOS transistor being supplied with the fuse reset signal;

5 an enabling fuse coupled between the first and second MOS transistors;

a first inverter for receiving a signal supplied between the enabling fuse and the second MOS transistor;

a third MOS transistor connected between an input
10 terminal of the first inverter and the ground voltage, gate of the third MOS transistor being coupled to an output terminal of the first inverter; and

a first NAND gate for receiving the enabling signal and an output signal from the first inverter and outputting the
15 fuse enabling signal.

11. The semiconductor device as recited in claim 10, the signal combination means includes:

a plurality of first NOR gates for receiving the fuse
20 enabling signal and the comparison signal output from the plurality of unit repair address comparing means;

a plurality of second NAND gates for receiving output signals from the plurality of first NOR gates;

a second NOR gate for receiving output signals from the
25 plurality of second NAND gates; and

a second inverter for receiving an output signal from the second NOR gate and outputting the repair signal.

12. The semiconductor device as recited in claim 11, the repair address comparison replica includes:

a third inverter for receiving the enabling signal;

a third NOR gate for delaying the comparison signal
5 output from the plurality of unit repair address comparing means by a delay value of the plurality of first NOR gates;

a second NAND gate for delaying an output signal from the third NOR gate by a delay value of the plurality of first NOR gates; and

10 a fourth NOR gate for delaying an output signal from the second NAND gate by a delay value of the second NOR gate.

13. The semiconductor device as recited in claim 12, the repair address comparison replica further includes an output
15 controller for adjusting phase and level of an output signal from the fourth NOR gate in order to equalize phase and level of an output signal from the fourth NOR gate with phase and level of the repair signal which is delivered from the repair address comparing means to the repair circuit controller.

20

14. The semiconductor device as recited in claim 1, the repair circuit controller includes:

at least one repair signal combination means for receiving the plurality of repair signals which is output from
25 the plurality of repair address comparing means and driving level of a repair sensing node in response to result of combining the plurality of repair signals;

a repair signal path replica for delaying the enabling signal which passes through the repair address comparison replica for a delay value until the repair signal combination means drives the level of the repair sensing node;

5 a first output means for outputting a redundancy circuit enabling signal which is used for operating the redundancy circuit in response to the level of the repair sensing node; and

a second output means for outputting a normal circuit
10 enabling signal which is used for operating a normal circuit in response to the level of the repair sensing node after it is enabled by the enabling signal which passes through the repair signal path replica.

15 15. The semiconductor device as recited in claim 14, the repair signal combination means includes:

a plurality of first NAND gates for receiving the plurality of repair signals;

a plurality of first NOR gates for receiving output
20 signals from the plurality of first NAND gates; and

at least one second NAND gate for receiving output signals from the plurality of first NOR gates and driving the level of repair sensing node.

25 16. The semiconductor device as recited in claim 15, the repair signal path replica includes:

a third NAND gate for delaying the enabling signal which

passes through the repair address comparison replica for a delay value of the first NAND gates;

a second NOR gate for delaying an output signal from the third NAND gate for delay value of the first NOR gate; and

5 a fourth NAND gate for delaying an output signal from the second NOR gate for a delay value of the second NAND gate.

17. The semiconductor device as recited in claim 16, the repair signal path replica further includes an output
10 controller for adjusting phase and level of an output signal from the fourth NAND gate in order to equalize phase and level of the repair sensing node.

18. The semiconductor device as recited in claim 17, the
15 second output means includes:

a fifth NOR gate for receiving the level of the repair sensing node and the enabling signal which is output from the repair signal path replica; and

a buffer for buffering an output signal of the fifth NOR
20 gate and outputting the normal circuit enabling signal.